G00002

ABSTRACT

METHOD USING ULTRAVIOLET RADIATION FOR INTEGRATED CIRCUIT MANUFACTURING

A method is provided for manufacturing an integrated circuit including a substrate with a gate layer and a gate dielectric provided on the substrate. The gate layer is formed into a gate using a process that imposes a charge in the gate dielectric. The substrate, gate, and gate dielectric are irradiated to discharge the charge across the gate dielectric.

FIGURE 4

162162